

isc Silicon NPN Power Transistor

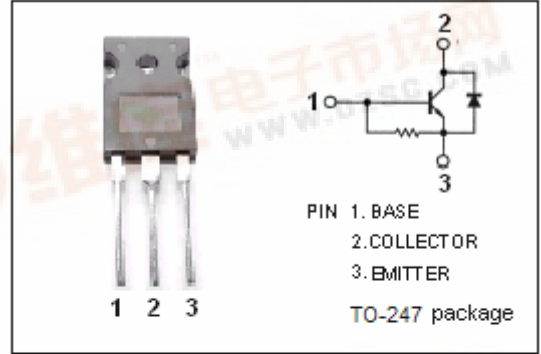
BU2725DW

DESCRIPTION

- High Switching Speed
- High Voltage
- Built-in Ddamper Ddiode

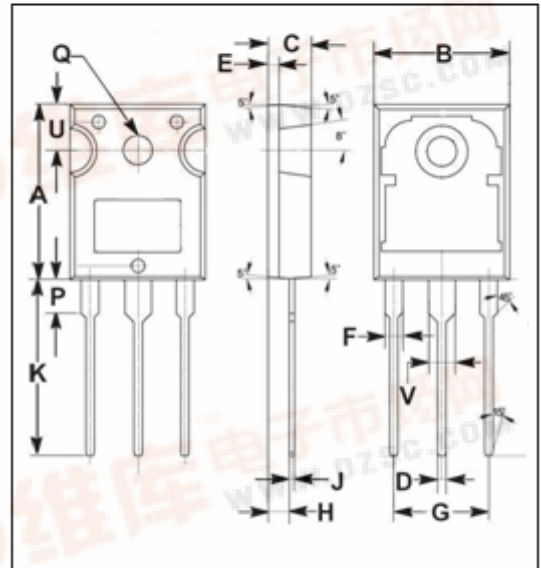
APPLICATIONS

- Designed for use in horizontal deflection circuits of color TV receivers.



ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CES}	Collector- Emitter Voltage(V _{BE} = 0)	1700	V
V _{EBO}	Emitter-Base Voltage	7.5	V
I _C	Collector Current- Continuous	12	A
I _{CM}	Collector Current-Peak	30	A
I _B	Base Current- Continuous	12	A
I _{BM}	Base Current-Peak	20	A
P _C	Collector Power Dissipation @ T _C =25°C	125	W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature Range	-65~150	°C



DIM	mm	
	MIN	MAX
A	19.80	20.20
B	15.40	15.80
C	4.90	5.10
D	0.90	1.10
E	1.40	1.60
F	1.90	2.10
G	10.80	11.00
H	2.40	2.60
J	0.50	0.70
K	19.50	20.50
P	3.90	4.10
Q	3.30	3.50
U	5.20	5.40
V	2.90	3.10

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal Resistance, Junction to Case	2.8	°C/W

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ELECTRICAL CHARACTERISTICS

 $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E=600\text{mA}; I_C=0$	7.5			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=7\text{A}; I_B=1.75\text{A}$			1.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=7\text{A}; I_B=1.75\text{A}$			0.95	V
I_{CES}	Collector Cutoff Current	$V_{CE}=1700\text{V}; V_{BE}=0$ $V_{CE}=1700\text{V}; V_{BE}=0; T_C=125^{\circ}\text{C}$			1.0 2.0	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=7.5\text{V}; I_C=0$		110		mA
h_{FE-1}	DC Current Gain	$I_C=1\text{A}; V_{CE}=5\text{V}$		19		
h_{FE-2}	DC Current Gain	$I_C=7\text{A}; V_{CE}=1\text{V}$	3.8		7.8	
V_{ECF}	C-E Diode Forward Voltage	$I_F=7\text{A}$			2.2	V